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(21) International Application Number: PCT/US96/14948 (22) International Filing Date: 18 September 1996 (18.09.96) (30) Priority Data: 08/530,648 20 September 1995 (20.09.95) US (71) Applicant: HOECHST CELANESE CORPORATION [US/US]; Route 202-206 North, Somerville, NJ 08876 (US). (72) Inventors: RAHMAN, Mr. Dali; 62 Concord Ridge Road, Flemington, NJ 08822 (US). AUBIN, Daniel; P.O. Box 276, 202 Congdon Road, Voluntown, CT 06384 (US). KHANNA, Dinesh, N.; Seven Sutton Farm Road, Flemington, NJ 08822 (US). DIXIT, Sunil; 50 Copper Penny Road, Flemington, NJ 08822 (US). (74) Agents: SAYKO, Andrew, F., Jr. et al.; Hoechst Celanese Corporation, 70 Meister Avenue, Somerville, NJ 08876 (US).		(81) Designated States: CN, JP, KR, SG, European patent (AT, BE, CH, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE). Published <i>With international search report. Before the expiration of the time limit for amending the claims and to be republished in the event of the receipt of amendments.</i>
(54) Title: FRACTIONATION OF PHENOL FORMALDEHYDE CONDENSATE AND PHOTORESIST COMPOSITIONS PRODUCED THEREFROM (57) Abstract A process for producing a water insoluble, aqueous alkali soluble, film forming novolak resin fraction having a low metal ion content, made by the fractionation of a phenol formaldehyde condensation product, a process for producing a photoresist composition containing such a novolak resin, and a method for producing a semiconductor device using such a photoresist composition.		